

Avionics Pulsed Power Transistor 500 W, 960 - 1215 MHz, 10 µs Pulse, 10 % Duty

Rev. V1

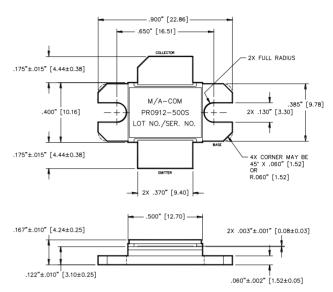
Features

- NPN silicon microwave power transistors
- Common base configuration
- · Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- · Hermetic metal/ceramic package
- RoHS* compliant

Absolute Maximum Ratings @ +25°C

Parameter	Symbol	Rating
Collector-Emitter Voltage	V _{CES}	80 V
Emitter-Base Voltage	V_{EBO}	3 V
Collector Current (Peak)	Ic	52.5 A
Power Dissipation	P _{TOT}	2.2 kW
Storage Temperature	T _{STG}	-65°C to +200°C
Junction Temperature	TJ	+200°C

Outline Drawing



UNLESS OTHERWISE NOTED, TOLERANCES ARE INCHES ±.005" [MILLIMETERS ±0.13mm]

Electrical Specifications: $V_{CC} = 50 \text{ V}$, $P_{IN} = 63 \text{ W}$, $T_A = 25 \pm 5^{\circ}\text{C}$ (unless otherwise noted)

Parameter	Symbol	Test Conditions	Units	Min.	Max.
Collector-Emitter Breakdown Voltage	BV _{CES}	$I_C = 80 \text{ mA}$	V	80	-
Collector-Emitter Leakage Current	I _{CES}	V _{CE} = 40 V	mA	-	15
Thermal Resistance	R _{TH(JC)}	F = 960, 1090, 1215 MHz	°C/W	-	0.08
Output Power	Po	F = 960, 1090, 1215 MHz	W	500	-
Power Gain	G₽	F = 960, 1090, 1215 MHz	dB	9	-
Collector Efficiency	h _C	F = 960, 1090, 1215 MHz	%	45	-
Input Return Loss	RL	F = 960, 1090, 1215 MHz	dB	-	-9
Load Mismatch Stability	VSWR-T	F = 960 MHz	-	-	3:1
Load Mismatch Tolerance	VSWR-S	F = 960, 1090, 1215 MHz	-	-	1.5:1

^{*} Restrictions on Hazardous Substances, European Union Directive 2011/65/EU.



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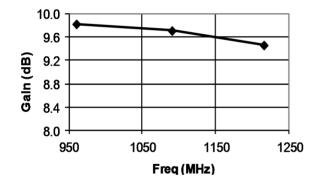
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Typical RF Performance

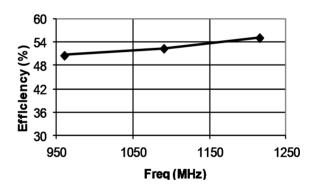
Freq.	P _{IN}	P _{OUT}	Gain	∆Gain	Ic	Eff	RL	VSWR-S (1.5:1)	VSWR-T (10:1)	P1dB Overdrive	
(MHz)	(W)	(W)	(dB)	(dB)	(A)	(%)	(dB)			P _{OUT} (W)	Δ P _o (dB)
960	63	598	9.77	_	23.5	50.9	-17.1	S	Р	675	0.52
1090	63	582	9.65	_	21.9	53.1	-21.8	S	_	677	0.66
1215	63	554	9.44	033	19.7	56.1	-16.8	S	_	619	0.48

Note: $\triangle Po(dB)$ is the difference between P_{OUT} at 1dB overdrive and P_{OUT} at P_{IN} = 63 W.

Gain vs. Frequency



Collector Efficiency vs. Frequency

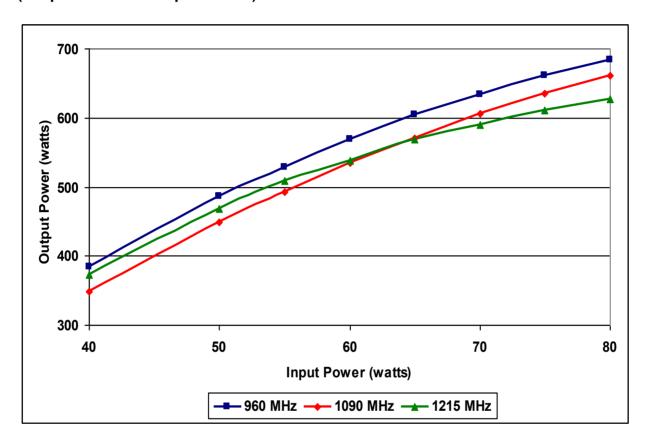




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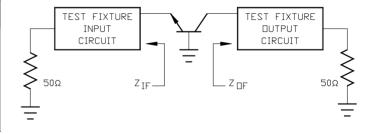
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RF Power Transfer Curve (Output Power)



Broadband Test Fixture Impedance

F (MHz)	Z _{IF} (Ω)	$Z_{OF}(\Omega)$		
960	1.3 - j1.4	1.27 - j1.4		
1025	1.3 - j1.1	1.2 - j1.1		
1090	1.2 - j0.9	1.3 - j0.9		
1150	1.2 - j0.8	1.4 - j0.7		
1215	1.0 - j0.8	1.3 - j0.6		

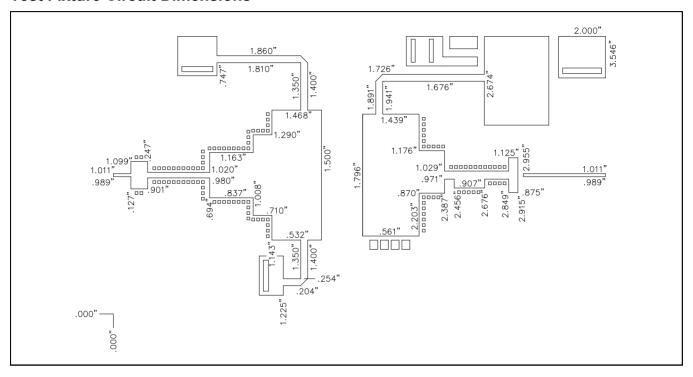




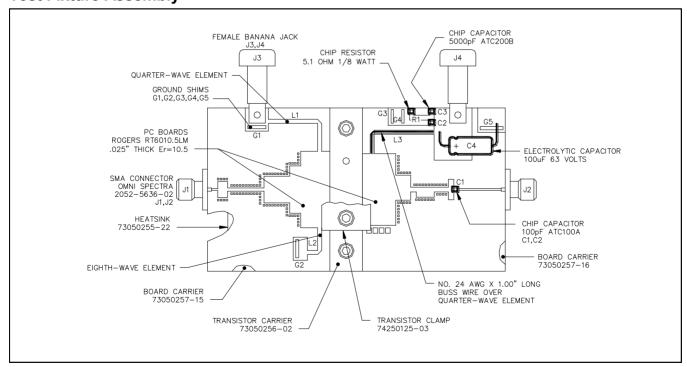
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Test Fixture Circuit Dimensions



Test Fixture Assembly





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